FM30H150G/T

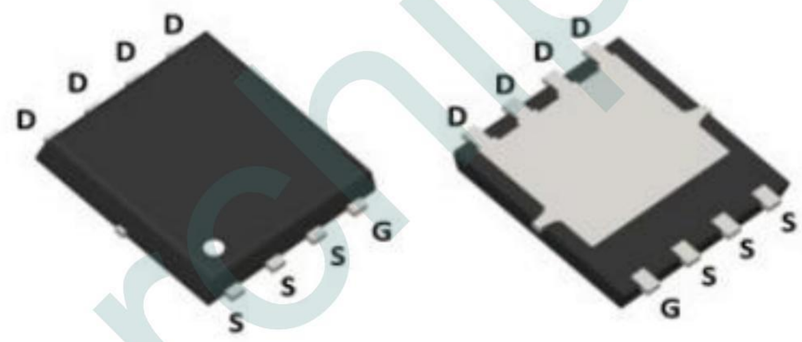
N-Channel Trench Power MOSFET

- 30V,150A
- $R_{DS(ON)}$=3.4mΩ (Typ.) @ V_{GS} =10V
- $R_{DS(ON)}$=4.0mΩ (Typ.) @ V_{GS} =4.5V
- Low on-state resistance
- Fast switching
- Lead free product

Application

- Load Switch
- PWM Application

Package



PDFN-8（5*6）

Absolute Maximum Ratings (T_C=25℃ unless otherwise specified)

Symbol	Parameter	Units	Maximum
V_{DS}	Drain-Source Voltage	V	30
V_{GS}	Gate-to-Source Voltage	V	±20
I_D @ T_C = 25°C	Continuous Drain Current	A	150
I_D @ T_C = 100°C	Continuous Drain Current	A	43
I_{DM}	Pulsed Drain Current	A	360
P_D	Power Dissipation	W	48
	Derating Factor	W/°C	0.26
E_{AS}	Single pulse avalanche energy○4	mJ	345
T_J	Operating Junction Temperature Range	°C	-55 to + 150
T_{STG}	Storage Temperature Range	°C	-55 to + 150

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